

What is claimed is:

1. An in-plane switching (IPS) mode liquid crystal display (LCD) device comprising:
 - 5 first and second substrates;
 - a plurality of gate and data lines crossing each other on the first substrate so as to define a plurality of pixel regions;
 - a thin film transistor formed at a crossing point of the gate and data lines;
 - a common line formed in the pixel region;
 - 10 a first electrode formed in the pixel region;
 - a second electrode formed in the pixel region in parallel to the first electrode, for being partially overlapped with the gate and data lines; and
 - a liquid crystal layer formed between the first and second substrates.
- 15 2. The IPS mode LCD device of claim 1, wherein the first electrode is a transparent electrode.
3. The IPS mode LCD device of claim 2, wherein the transparent electrode is formed of ITO (indium tin oxide).
- 20 4. The IPS mod LCD device of claim 1, wherein the first electrode is a common electrode, and the second electrode is a data electrode.
5. The IPS mode LCD device of claim 1, further comprising:

a passivation layer having a hole and deposited on an entire surface of the first substrate;

a first alignment layer deposited on the passivation layer;

a black matrix layer formed on the second substrate;

5 a color filter layer formed on the black matrix layer; and

a second alignment layer formed on the color filter layer.

6. The IPS mode LCD device of claim 1, wherein the thin film transistor includes:

10 a gate electrode formed on the first substrate;

a gate insulating layer formed on the gate electrode;

a semiconductor layer formed on the gate insulating layer; and

source and drain electrodes formed on the semiconductor layer.

15 7. The IPS mode LCD device of claim 6, wherein the gate insulating layer is formed on the entire surface of the first substrate.

8. The IPS mode LCD device of claim 7, wherein the second electrode is formed on the gate insulating layer.

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9. The IPS mode LCD device of claim 5, wherein the first electrode is formed on the passivation layer.

10. The IPS mode LCD device of claim 1, further comprising:

a first metal line being in contact with the first electrode on the passivation layer of the common line region; and

a second metal line being in contact with the second electrode on the gate insulating layer of the common line region.

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11. The IPS mode LCD device of claim 10, wherein the first metal line is formed of the same metal material as the first electrode.

12. The IPS mode LCD device of claim 10, wherein the second metal line is
10 formed of the same metal material as the second electrode.

13. The IPS mode LCD device of claim 10, wherein the first and second electrodes form a storage capacity.

14. The IPS mode LCD device of claim 11, wherein the first metal line is in
15 contact with the common line through the hole.

15. The IPS mode LCD device of claim 5, wherein the first alignment layer is formed of polyimide or photo-reactive material.

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16. The IPS mode LCD device of claim 15, wherein the photo-reactive material is selected from any one of PVCN (polyvinylcinnamate) or polysiloxane based materials.

17. The IPS mode LCD device of claim 5, further comprising an overcoat layer deposited on the color filter layer.

18. The IPS mode LCD device of claim 5, wherein the second alignment layer is
5 formed of polyimide or photo-reactive material.

19. The IPS mode LCD device of claim 18, wherein the photo-reactive material is selected from any one of PVCN (polyvinylcinnamate) or polysiloxane based materials.

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20. An in-plane switching (IPS) mode liquid crystal display (LCD) device comprising:

first and second substrates;

a plurality of gate and data lines crossing each other on the first substrate so as

15 to define a plurality of pixel regions;

a thin film transistor at a crossing point of the gate and data lines;

a common line formed in the pixel region;

a first electrode formed in the pixel region;

a second electrode formed in the pixel region in parallel to the first electrode for

20 being partially overlapped with the gate and data lines, of which a crossing portion with the first electrode is formed in a slanting structure; and

a liquid crystal layer formed between the first and second substrates.

21. The IPS mode LCD device of claim 20, wherein the first electrode is a

transparent electrode.

22. The IPS mode LCD device of claim 21, wherein the transparent electrode is formed of ITO (indium tin oxide).

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23. The IPS mode LCD device of claim 20, wherein the first electrode is a common electrode, and the second electrode is a data electrode.

24. The IPS mode LCD device of claim 20, further comprising:

10 a passivation layer having a hole and deposited on an entire surface of the first substrate;

a first alignment layer deposited on the passivation layer;

a black matrix layer formed on the second substrate;

a color filter layer formed on the black matrix layer; and

15 a second alignment layer formed on the color filter layer.

25. The IPS mode LCD device of claim 20, wherein the thin film transistor includes:

a gate electrode formed on the first substrate;

20 a gate insulating layer formed on the gate electrode;

a semiconductor layer formed on the gate insulating layer; and

source and drain electrodes formed on the semiconductor layer.

26. The IPS mode LCD device of claim 25, wherein the gate insulating layer is

formed on an entire surface of the first substrate.

27. The IPS mode LCD device of claim 26, wherein the second electrode is formed on the gate insulating layer.

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28. The IPS mode LCD device of claim 24, wherein the first electrode is formed on the passivation layer.

29. The IPS mode LCD device of claim 20, further comprising:

10 a first metal line being in contact with the first electrode on the passivation layer of the common line region; and

a second metal line being in contact with the second electrode on the gate insulating layer of the common line region.

15 30. The IPS mode LCD device of claim 29, wherein the first metal line is formed of the same metal material as the first electrode.

31. The IPS mode LCD device of claim 29, wherein the second metal line is formed of the same metal material as the second electrode.

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32. The IPS mode LCD device of claim 29, wherein the first and second electrodes form a storage capacity.

33. The IPS mode LCD device of claim 30, wherein the first metal line is in

contact with the common line through the hole.

34. The IPS mode LCD device of claim 24, wherein the first alignment layer is formed of polyimide or photo-reactive material.

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35. The IPS mode LCD device of claim 34, wherein the photo-reactive material is selected from any one of PVCN (polyvinylcinnamate) or polysiloxane based materials.

10 36. The IPS mode LCD device of claim 24, further comprising an overcoat layer deposited on the color filter layer.

37. The IPS mode LCD device of claim 24, wherein the second alignment layer is formed of polyimide or photo-reactive material.

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38. The IPS mode LCD device of claim 37, wherein the photo-reactive material is selected from any one of PVCN (polyvinylcinnamate) or polysiloxane based materials.

20 39. The IPS mode LCD device of claim 20, wherein an alignment direction of the alignment layer is θ_R , the both sides of the second electrode have the slanting structure forming angles of θ_A and θ_B to the center of the first electrode.

40. The IPS mode LCD device of claim 39, wherein $\theta_R < \theta_A < \theta_R + 90^\circ$, and $90^\circ -$

$$\theta_R < \theta_B < 180^\circ - \theta_R.$$

41. The IPS mode LCD device of claim 39, wherein $\theta_A = 45^\circ$, and $\theta_B = 45^\circ$.